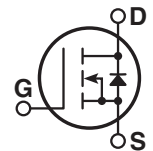
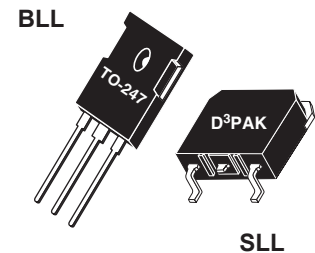


## POWER MOS 7 MOSFET

Power MOS 7<sup>®</sup> is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETS. Both conduction and switching losses are addressed with Power MOS 7<sup>®</sup> by significantly lowering  $R_{DS(ON)}$  and  $Q_g$ . Power MOS 7<sup>®</sup> combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge,  $Q_g$
- Increased Power Dissipation
- Easier To Drive
- TO-247 or Surface Mount D<sup>3</sup>PAK Package



### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT10090	UNIT
$V_{DSS}$	Drain-Source Voltage	1000	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	12	Amps
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	48	
$V_{GS}$	Gate-Source Voltage Continuous	$\pm 30$	Volts
$V_{GSM}$	Gate-Source Voltage Transient	$\pm 40$	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	298	Watts
	Linear Derating Factor	2.4	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	
$I_{AR}$	Avalanche Current <sup>1</sup> (Repetitive and Non-Repetitive)	12	Amps
$E_{AR}$	Repetitive Avalanche Energy <sup>1</sup>	30	mJ
$E_{AS}$	Single Pulse Avalanche Energy <sup>4</sup>	1210	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )	1000			Volts
$I_{D(on)}$	On State Drain Current <sup>2</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ )	12			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance <sup>2</sup> ( $V_{GS} = 10V, 6A$ )			0.95	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = 1000V, V_{GS} = 0V$ )			100	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 800V, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )			500	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 1mA$ )	3		5	Volts



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

**DYNAMIC CHARACTERISTICS**

**APT10090BLL - SLL**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1 MHz		1969		pF
C <sub>oss</sub>	Output Capacitance			332		
C <sub>rss</sub>	Reverse Transfer Capacitance			55		
Q <sub>g</sub>	Total Gate Charge <sup>3</sup>	V <sub>GS</sub> = 10V V <sub>DD</sub> = 500V I <sub>D</sub> = 12A @ 25°C		71		nC
Q <sub>gs</sub>	Gate-Source Charge			12		
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge			47		
t <sub>d(on)</sub>	Turn-on Delay Time	<b>RESISTIVE SWITCHING</b> V <sub>GS</sub> = 15V V <sub>DD</sub> = 500V I <sub>D</sub> = 12A @ 25°C R <sub>G</sub> = .6Ω		9		ns
t <sub>r</sub>	Rise Time			5		
t <sub>d(off)</sub>	Turn-off Delay Time			23		
t <sub>f</sub>	Fall Time ≤			4		
E <sub>on</sub>	Turn-on Switching Energy <sup>6</sup>	<b>INDUCTIVE SWITCHING @ 25°C</b> V <sub>DD</sub> = 670V, V <sub>GS</sub> = 15V I <sub>D</sub> = 12A, R <sub>G</sub> = 5Ω		334		μJ
E <sub>off</sub>	Turn-off Switching Energy			77		
E <sub>on</sub>	Turn-on Switching Energy <sup>6</sup>	<b>INDUCTIVE SWITCHING @ 125°C</b> V <sub>DD</sub> = 670V, V <sub>GS</sub> = 15V I <sub>D</sub> = 12A, R <sub>G</sub> = 5Ω		672		
E <sub>off</sub>	Turn-off Switching Energy			100		

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I <sub>S</sub>	Continuous Source Current (Body Diode)			12	Amps
I <sub>SM</sub>	Pulsed Source Current <sup>1</sup> (Body Diode)			48	
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup> (V <sub>GS</sub> = 0V, I <sub>S</sub> = -I <sub>D</sub> 12A)			1.3	Volts
t <sub>rr</sub>	Reverse Recovery Time (I <sub>S</sub> = -I <sub>D</sub> 12A, di <sub>S</sub> /dt = 100A/μs)		700		ns
Q <sub>rr</sub>	Reverse Recovery Charge (I <sub>S</sub> = -I <sub>D</sub> 12A, di <sub>S</sub> /dt = 100A/μs)		9.0		μC
dv <sub>dt</sub>	Peak Diode Recovery dv <sub>dt</sub> <sup>5</sup>			10	V/ns

**THERMAL CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Junction to Case			0.42	°C/W
R <sub>θJA</sub>	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%

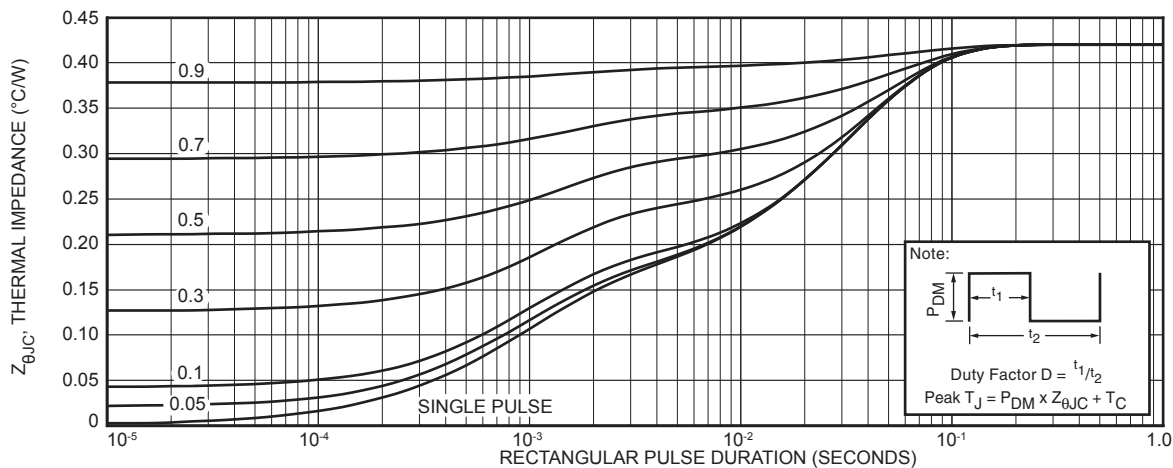
③ See MIL-STD-750 Method 3471

④ Starting T<sub>j</sub> = +25°C, L = 16.81mH, R<sub>G</sub> = 25Ω, Peak I<sub>L</sub> = 12A

⑤ dv<sub>dt</sub> numbers reflect the limitations of the test circuit rather than the device itself. I<sub>S</sub> ≤ -I<sub>D</sub> 12A di<sub>S</sub>/dt ≤ 700A/μs V<sub>R</sub> ≤ V<sub>DSS</sub> T<sub>J</sub> ≤ 150°C

⑥ Eon includes diode reverse recovery measured in accordance with JEDEC standard JESD24-1. See figures 18, 20.

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.



**FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION**

# Typical Performance Curves

APT10090BLL - SLL

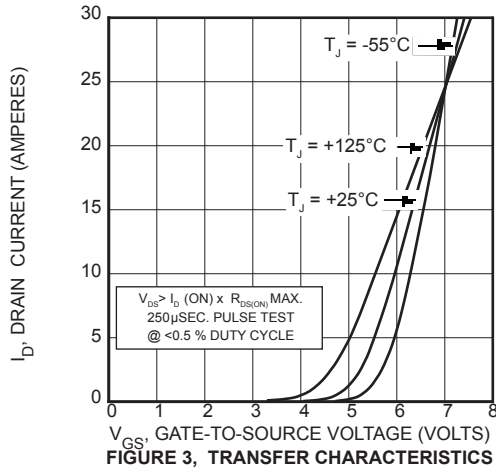


FIGURE 3, TRANSFER CHARACTERISTICS

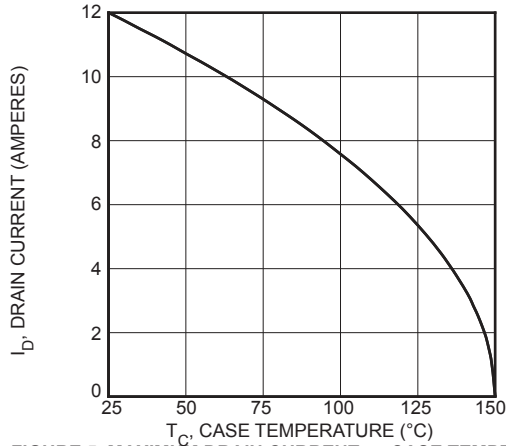


FIGURE 5, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

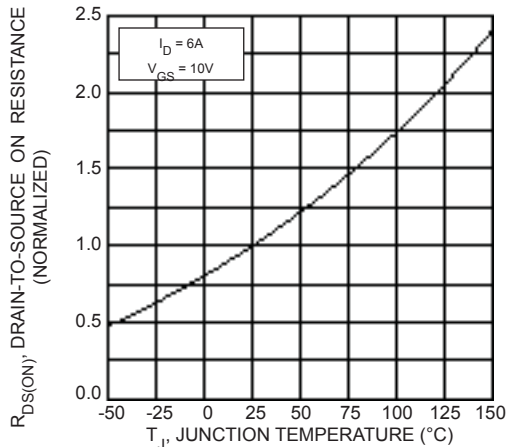


FIGURE 7,  $R_{DS(\text{ON})}$  vs. TEMPERATURE

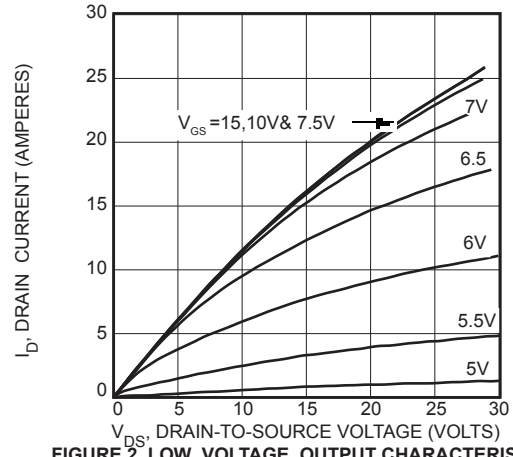


FIGURE 2, LOW VOLTAGE OUTPUT CHARACTERISTICS

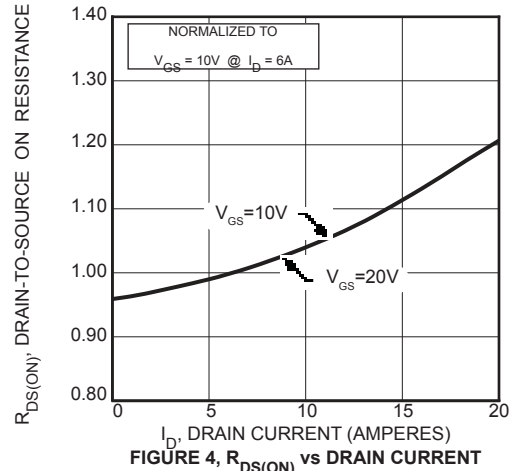


FIGURE 4,  $R_{DS(\text{ON})}$  vs DRAIN CURRENT

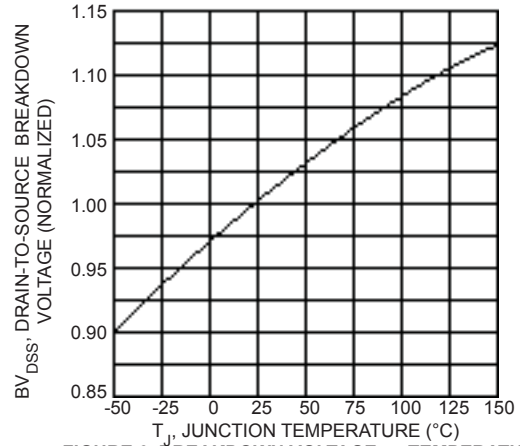


FIGURE 6, BREAKDOWN VOLTAGE vs TEMPERATURE

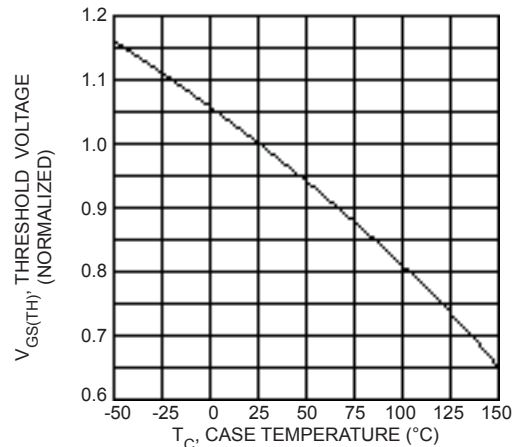


FIGURE 8, THRESHOLD VOLTAGE vs TEMPERATURE

# Typical Performance Curves

APT10090BLL - SLL

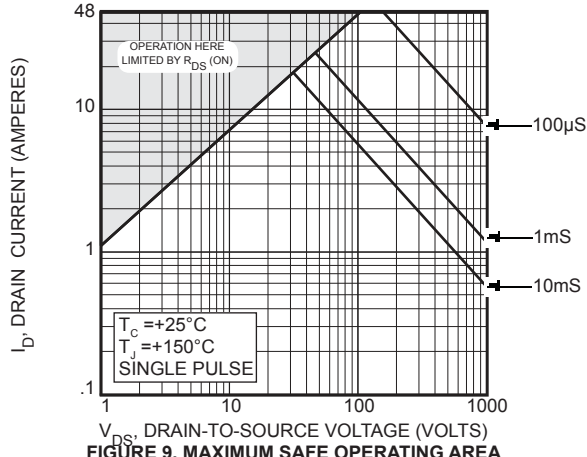


FIGURE 9, MAXIMUM SAFE OPERATING AREA

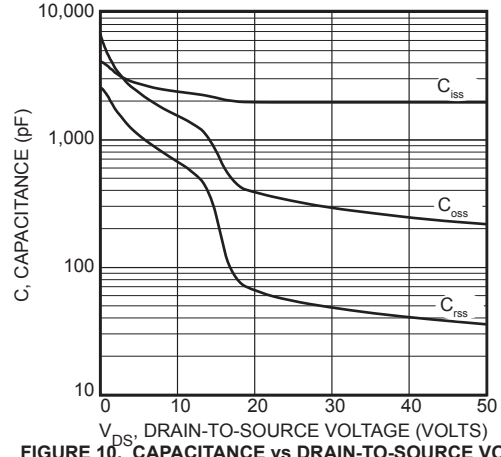


FIGURE 10, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

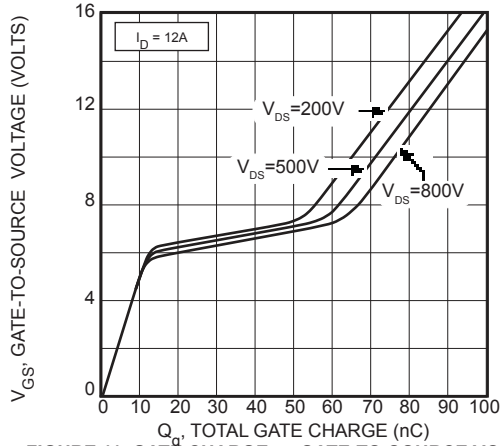


FIGURE 11, GATE CHARGE vs GATE-TO-SOURCE VOLTAGE

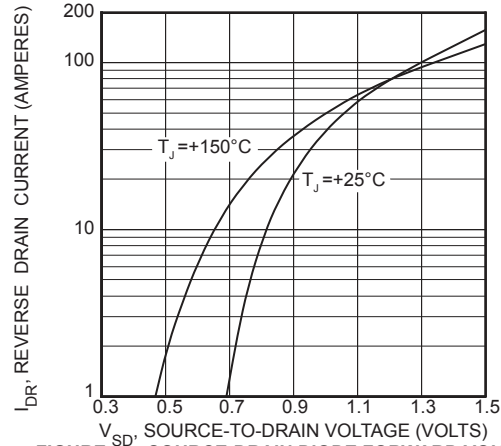


FIGURE 12, SOURCE-DRAIN DIODE FORWARD VOLTAGE

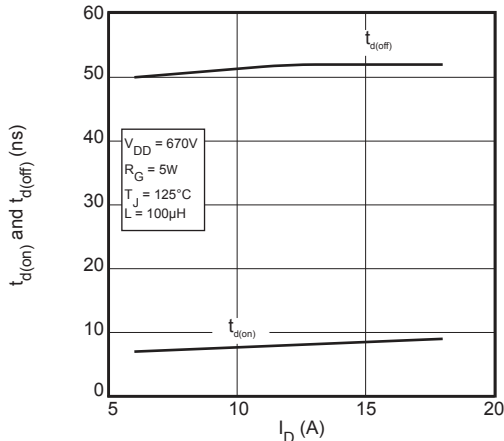


FIGURE 13, DELAY TIMES vs CURRENT

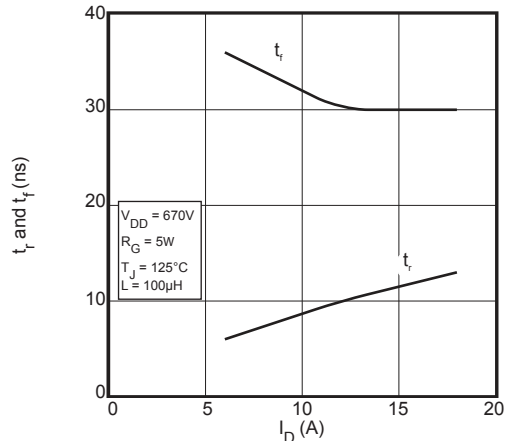


FIGURE 14, RISE AND FALL TIMES vs CURRENT

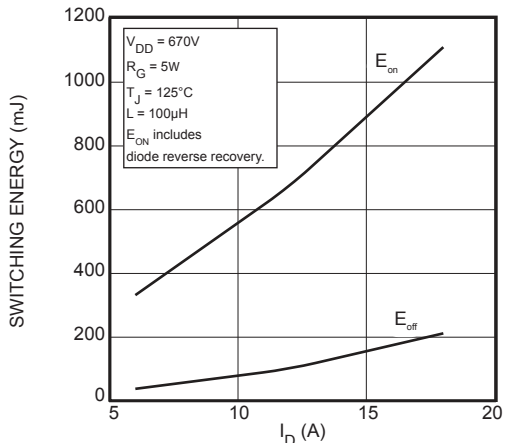


FIGURE 15, SWITCHING ENERGY vs CURRENT

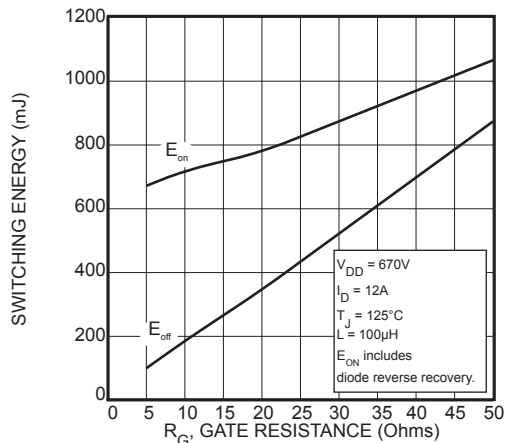


FIGURE 16, SWITCHING ENERGY vs. GATE RESISTANCE

### Typical Performance Curves

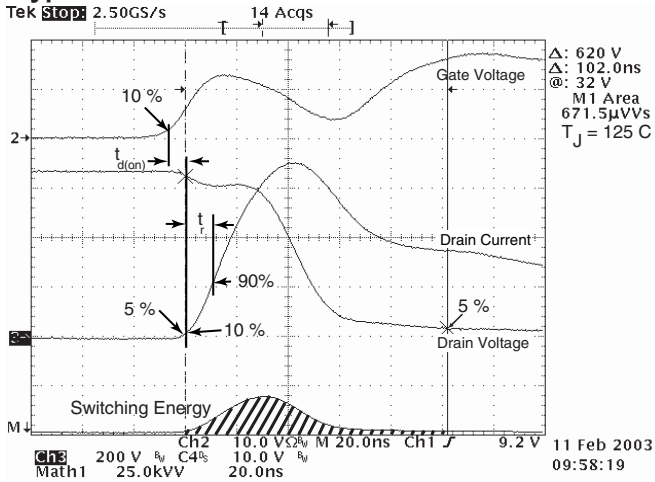


Figure 17, Turn-on Switching Waveforms and Definitions

### APT10090BLL - SLL

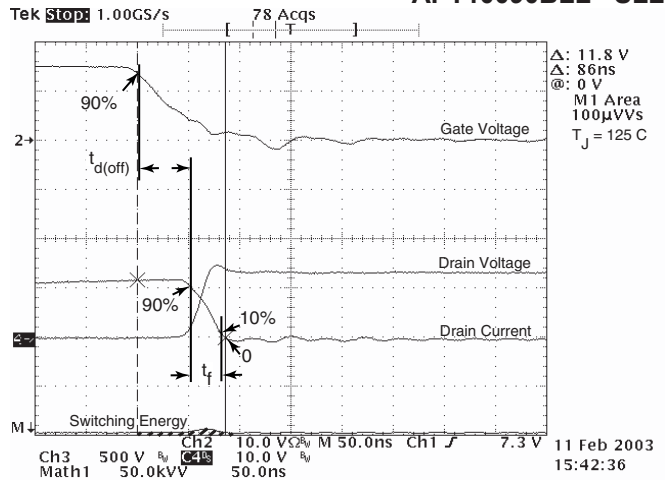


Figure 18, Turn-off Switching Waveforms and Definitions

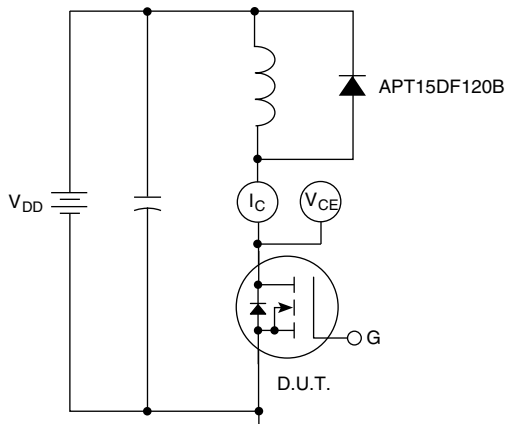
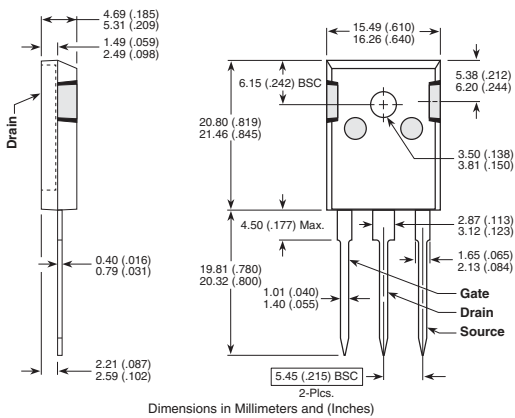


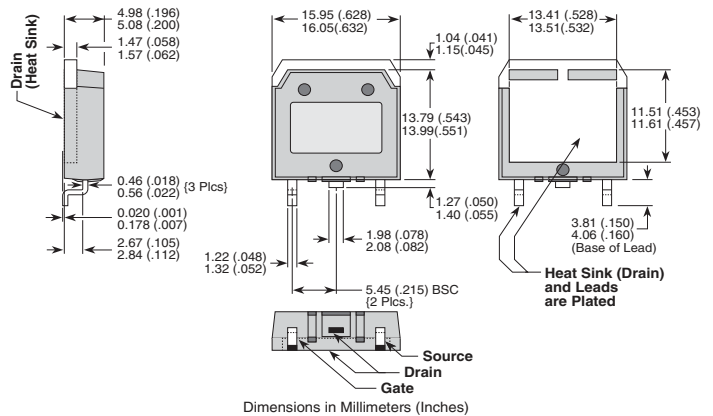
Figure 19, Inductive Switching Test Circuit

### TO-247 (B) Package Outline



### D<sup>3</sup>PAK Package Outline

e3 100% Sn Plated



Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743, 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. US and Foreign patents pending. All Rights Reserved.